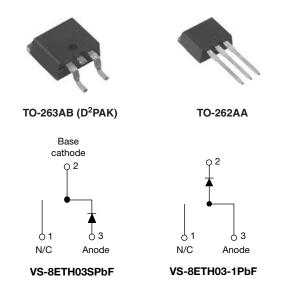
VS-8ETH03SPbF, VS-8ETH03-1PbF



RoHS

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Hyperfast Rectifier, 8 A FRED Pt®



PRODUCT SUMMARY						
Package	TO-263AB (D ² PAK), TO-262AA					
I _{F(AV)}	8 A					
V _R	300 V					
V _F at I _F	0.83 V					
t _{rr}	35 ns					
T _J max.	175 °C					
Diode variation	Single die					

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum compliant peak of 260 °C
 FREE
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Repetitive peak reverse voltage	V _{RRM}		300	V		
Average rectified forward current	I _{F(AV)}	T _C = 155 °C	8	٨		
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	100	A		
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX.							
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	300	-	-		
Forward voltage	V _F	I _F = 8 A	-	1.0	1.25	V	
		I _F = 8 A, T _J = 125 °C	-	0.83	1.00		
Poverse leakage ourrent		V _R = V _R rated	-	0.02	20		
Reverse leakage current I _R		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	6.0	200	μA	
Junction capacitance	CT	V _R = 300 V	-	31	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	

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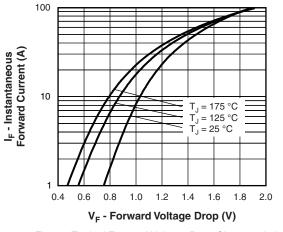
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DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 A, dI_F/dt = -$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = -50 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		-	35		
Reverse recovery time	t _{rr}	T _J = 25 °C	- I _F = 8 A dI _F /dt = - 200 A/μs V _R = 200 V -	-	27	-	ns	
		T _J = 125 °C		-	40	-		
Deck receiver ourrent	$I_{RRM} = \frac{T_J = 25 \text{ °C}}{T_J = 125 \text{ °C}}$	T _J = 25 °C		-	2.2	-	А	
Peak recovery current		T _J = 125 °C		-	5.3	-	~	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	30	-	nC	
		T _J = 125 °C		-	106	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	1.45	2.5		
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-		
Weight			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
		Case style TO-263AB (D ² PAK)	8ETH03S			-	
Marking device		Case style TO-262	8ETH03-1				

VS-8ETH03SPbF, VS-8ETH03-1PbF

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Fig. 1 - Typical Forward Voltage Drop Characteristics

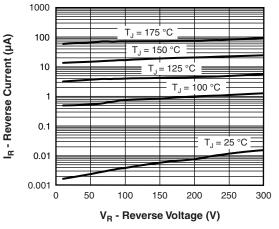


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

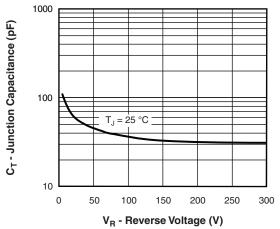


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

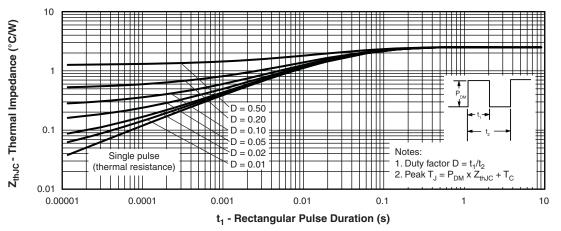


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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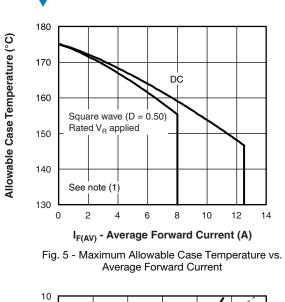
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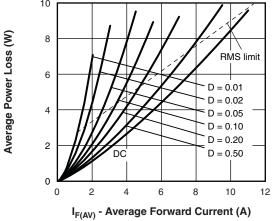
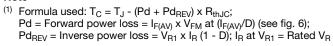
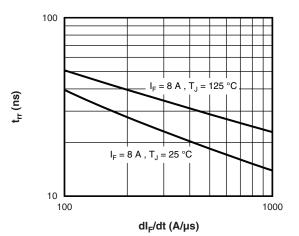


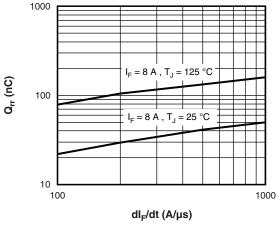
Fig. 6 - Forward Power Loss Characteristics

Note











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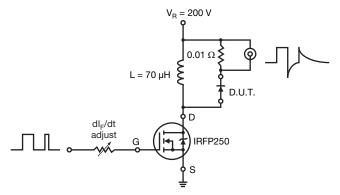
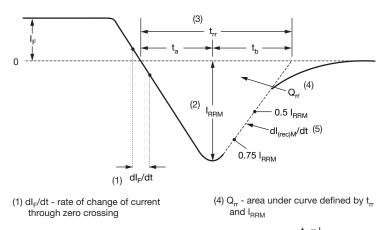


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$ (5) dI_{(rec)M}/dt peak rate of change of

current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

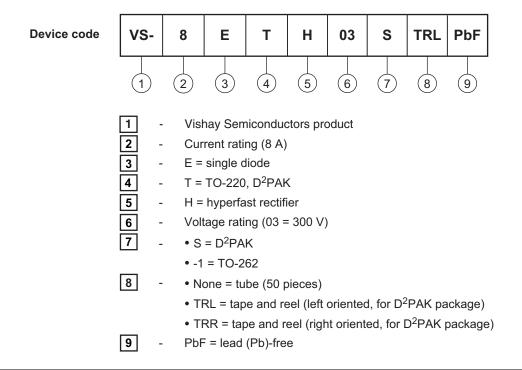


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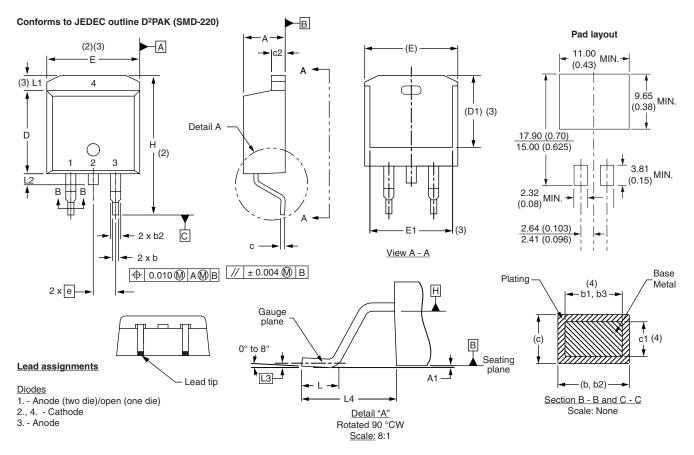
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LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95014						
Part marking information	www.vishay.com/doc?95008					
Packaging information	www.vishay.com/doc?95032					

Vishay Semiconductors

D²PAK, TO-262



DIMENSIONS - D²PAK in millimeters and inches

SHA

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
с	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL					NOTES
STWIDUL	MIN.	MAX.	MIN.	MAX.	NULES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100	BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	SC 0.010		
L4	4.78	5.28	0.188	0.208	

INCHES

NOTES

MILLIMETERS

⁽⁷⁾ Outline conforms to JEDEC outline TO-263AB

SYMBOL

Notes

 $^{(1)}\,$ Dimensioning and tolerancing per ASME Y14.5 M-1994 $\,$

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

- $^{(3)}\,$ Thermal pad contour optional within dimension E, L1, D1 and E1
- ⁽⁴⁾ Dimension b1 and c1 apply to base metal only
- ⁽⁵⁾ Datum A and B to be determined at datum plane H
- ⁽⁶⁾ Controlling dimension: inch

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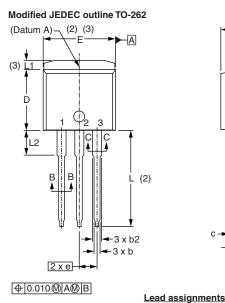
Outline Dimensions

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D²PAK, TO-262



DIMENSIONS - TO-262 in millimeters and inches

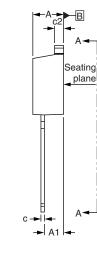


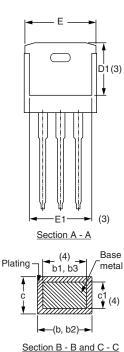
Lead tip

Diodes

3. - Anode

2., 4. - Cathode





Scale: None

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the

SYMBOL	MILLIMETERS		INC	INCHES		
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54	2.54 BSC		0 BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

1. - Anode (two die)/open (one die)

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Controlling dimension: inches

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actual package outline

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